Document Number: MC9S08PA4

Rev. 2, 12/20/2012

MC9S08PA4

MC9S08PA4 Series

Supports: MC9S08PA4 Key features

- 8-Bit S08 central processor unit (CPU)
 - Up to 20 MHz bus at 2.7 V to 5.5 V across temperature range of -40 °C to 105 °C
 - Supporting up to 40 interrupt/reset sources
 - Supporting up to four-level nested interrupt
 - On-chip memory
 - Up to 4 KB flash read/program/erase over full operating voltage and temperature
 - Up to 128 byte EEPROM; 2-byte erase sector; program and erase while executing flash
 - Up to 512 byte random-access memory (RAM)
 - Flash and RAM access protection
- · Power-saving modes
 - One low-power stop mode; reduced power wait mode
 - Peripheral clock enable register can disable clocks to unused modules, reducing currents; allows clocks to remain enabled to specific peripherals in stop3 mode
- Clocks
 - Oscillator (XOSC) loop-controlled Pierce oscillator; crystal or ceramic resonator range of 31.25 kHz to 39.0625 kHz or 4 MHz to 20 MHz
 - Internal clock source (ICS) containing a frequency-locked-loop (FLL) controlled by internal or external reference; precision trimming of internal reference allowing 1% deviation across temperature range of 0 °C to 70 °C and 2% deviation across temperature range of -40 °C to 105 °C; up to 20 MHz
- · System protection
 - Watchdog with independent clock source
 - Low-voltage detection with reset or interrupt; selectable trip points
 - Illegal opcode detection with reset
 - Illegal address detection with reset

Development support

- Single-wire background debug interface
- Breakpoint capability to allow three breakpoints setting during in-circuit debugging
- On-chip in-circuit emulator (ICE) debug module containing two comparators and nine trigger modes

Peripherals

- ACMP one analog comparator with both positive and negative inputs; separately selectable interrupt on rising and falling comparator output; filtering
- ADC 8-channel, 12-bit resolution; 2.5 µs conversion time; data buffers with optional watermark; automatic compare function; internal bandgap reference channel; operation in stop mode; optional hardware trigger
- FTM two 2-channel flex timer modulators modules; 16-bit counter; each channel can be configured for input capture, output compare, edge- or center-aligned PWM mode
- RTC 16-bit real timer counter (RTC)
- SCI one serial communication interface (SCI/ UART) modules optional 13-bit break; full duplex non-return to zero (NRZ); LIN extension support
- Input/Output
 - 18 GPIOs including one output-only pin
 - One 8-bit keyboard interrupt module (KBI)
 - Two, ultra-high current sink pins supporting 20 mA source/sink current
- Package options
 - 20-pin SOIC
 - 16-pin TSSOP

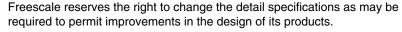




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1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to www.freescale.com and perform a part number search for the following device numbers: PA4.

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

MC 9 S08 PA AA B CC

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
MC	Qualification status	MC = fully qualified, general market flow
9	Memory	• 9 = flash based
S08	Core	• S08 = 8-bit CPU
PA	Device family	• PA
AA	Approximate flash size in KB	4 = 4 KB2 = 2 KB
В	Temperature range (°C)	• V = -40 to 105
CC	Package designator	WJ = 20-SOICTG = 16-TSSOP

2.4 Example

This is an example part number:

MC9S08PA4VWJ

3 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding, the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 1. Parameter Classifications

Р	Those parameters are guaranteed during production testing on each individual device.
С	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
Т	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled "C" in the parameter tables where appropriate.

4 Ratings

4.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T _{STG}	Storage temperature	- 55	150	°C	1
T _{SDR}	Solder temperature, lead-free	_	260	°C	2

- 1. Determined according to JEDEC Standard JESD22-A103, High Temperature Storage Life.
- 2. Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level		3	_	1

Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	-6000	+6000	V	1
V _{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	
I _{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	

Determined according to JEDEC Standard JESD22-A114, Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM).

4.4 Voltage and current operating ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in below table may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this document.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}) or the programmable pullup resistor associated with the pin is enabled.

Symbol	Description	Min.	Max.	Unit
V_{DD}	Supply voltage	-0.3	5.8	V
I _{DD}	Maximum current into V _{DD}	_	120	mA
V_{DIO}	Digital input voltage (except RESET, EXTAL, and XTAL)	-0.3	V _{DD} + 0.3	V
V _{AIO}	Analog ¹ , RESET, EXTAL, and XTAL input voltage	-0.3	V _{DD} + 0.3	V
I _D	Instantaneous maximum current single pin limit (applies to all port pins)	-25	25	mA
V_{DDA}	Analog supply voltage	V _{DD} – 0.3	V _{DD} + 0.3	V

General

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5 General

5.1 Nonswitching electrical specifications

5.1.1 DC characteristics

This section includes information about power supply requirements and I/O pin characteristics.

Table 2. DC characteristics

Symbol	С	Descriptions			Min	Typical ¹	Max	Unit
_	_	Ope	rating voltage	_	2.7	_	5.5	V
V _{OH}	Р	Output high voltage	All I/O pins, standard- drive strength	5 V, I _{load} = -5 mA	V _{DD} - 0.8	_	_	V
	С			3 V, I _{load} = -2.5 mA	V _{DD} - 0.8	_	_	V
	Р		High current drive pins, high-drive	5 V, I _{load} = -20 mA	V _{DD} - 0.8	_	_	V
	С		strength ²	3 V, I _{load} = -10 mA	V _{DD} - 0.8	_	_	V
I _{OHT}	D	Output high	Max total I _{OH} for all	5 V	_	_	-100	mA
		current	ports	3 V	_	_	-50	
V _{OL}	Р	Output low voltage	All I/O pins, standard- drive strength	5 V, I _{load} = 5 mA	_	_	0.8	V
	С			3 V, I _{load} = 2.5 mA	_	_	0.8	V
	Р		High current drive pins, high-drive	5 V, I _{load} =20 mA	_	_	0.8	V
	С		strength ²	3 V, I _{load} = 10 mA	_	_	0.8	V
I _{OLT}	D	Output low	Max total I _{OL} for all	5 V	_	_	100	mA
		current	ports	3 V	_	_	50	
V _{IH}	Р	Input high	All digital inputs	V _{DD} >4.5V	$0.70 \times V_{DD}$	_	_	V
		voltage		V _{DD} >2.7V	$0.75 \times V_{DD}$	_	_	
V _{IL}	Р	Input low	All digital inputs	V _{DD} >4.5V	_	_	$0.30 \times V_{DD}$	V
		voltage		V _{DD} >2.7V	_	_	$0.35 \times V_{DD}$	
V _{hys}	С	Input hysteresis	All digital inputs		$0.06 \times V_{DD}$	_	_	mV

Table 2. DC characteristics (continued)

Symbol	С		Descriptions		Min	Typical ¹	Max	Unit
II _{In} I	Р	Input leakage current			_	0.1	1	μА
II _{OZ} I	Р	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		$V_{IN} = V_{DD}$ or V_{SS}	_	0.1	1	μА
ll _{OZTOT} l	С	Total leakage combined for all inputs and Hi-Z pins	All input only and I/O	$V_{IN} = V_{DD}$ or V_{SS}	_	_	2	μА
R _{PU}	P Pullup resistors		All digital inputs, when enabled (all I/O pins other than PTA5/ IRQ/TCLK/RESET		30.0	_	50.0	kΩ
R _{PU} ³	Р	Pullup resistors	PTA5/IRQ/TCLK/ RESET	_	30.0	_	50.0	kΩ
I _{IC}	D	DC injection	Single pin limit	$V_{IN} < V_{SS}$	-0.2	_	2	mA
		current ^{4, 5, 6}	Total MCU limit, includes sum of all stressed pins	$V_{IN} > V_{DD}$	-5	_	25	
C _{In}	С	Input cap	acitance, all pins	_		_	7	pF
V _{RAM}	С	RAM re	etention voltage	_	2.0	_		V

- 1. Typical values are measured at 25 °C. Characterized, not tested.
- 2. Only PTB4, PTB5 support ultra high current output.
- 3. The specified resistor value is the actual value internal to the device. The pullup value may appear higher when measured externally on the pin.
- 4. All functional non-supply pins, except for PTA5, are internally clamped to V_{SS} and V_{DD} .
- 5. Input must be current-limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the large one.
- 6. Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If the positive injection current ($V_{In} > V_{DD}$) is higher than I_{DD} , the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure that external V_{DD} load will shunt current higher than maximum injection current when the MCU is not consuming power, such as no system clock is present, or clock rate is very low (which would reduce overall power consumption).

Table 3. LVD and POR Specification

Symbol	С	Description	Min	Тур	Max	Unit
V _{POR}	D	POR re-arm voltage ^{1, 2}	1.5	1.75	2.0	V
V _{LVDH}	С	Falling low-voltage detect threshold - high range (LVDV = 1) ³	4.2	4.3	4.4	V

Nonswitching electrical specifications

Table 3. LVD and POR Specification (continued)

Symbol	С	Descr	iption	Min	Тур	Max	Unit
V _{LVW1H}	С	Falling low- voltage	Level 1 falling (LVWV = 00)	4.3	4.4	4.5	V
V _{LVW2H}	С	warning threshold - high range	Level 2 falling (LVWV = 01)	4.5	4.5	4.6	V
V _{LVW3H}	С	Iligii railige	Level 3 falling (LVWV = 10)	4.6	4.6	4.7	V
V _{LVW4H}	С		Level 4 falling (LVWV = 11)	4.7	4.7	4.8	V
V _{HYSH}	С		High range low-voltage detect/warning hysteresis		100	_	mV
V _{LVDL}	С	threshold - low	Falling low-voltage detect threshold - low range (LVDV = 0)		2.61	2.66	V
V _{LVDW1L}	С	Falling low- voltage	Level 1 falling (LVWV = 00)	2.62	2.7	2.78	V
V _{LVDW2L}	С	warning threshold - low range	Level 2 falling (LVWV = 01)	2.72	2.8	2.88	V
V _{LVDW3L}	С	low range	Level 3 falling (LVWV = 10)	2.82	2.9	2.98	V
V _{LVDW4L}	С		Level 4 falling (LVWV = 11)	2.92	3.0	3.08	V
V _{HYSDL}	С		Low range low-voltage detect hysteresis		40	_	mV
V _{HYSWL}	С		Low range low-voltage warning hysteresis		80	_	mV
V_{BG}	Р	Buffered band	dgap output 4	1.14	1.16	1.18	V

- 1. Maximum is highest voltage that POR is guaranteed.
- 2. POR ramp time must be longer than 20us/V to get a stable startup.
- 3. Rising thresholds are falling threshold + hysteresis.
- 4. Voltage factory trimmed at V_{DD} = 5.0 V, Temp = 25 °C

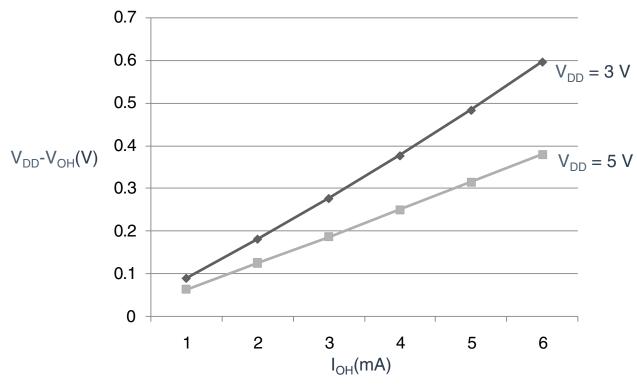


Figure 1. Typical I_{OH} Vs. V_{DD}-V_{OH}

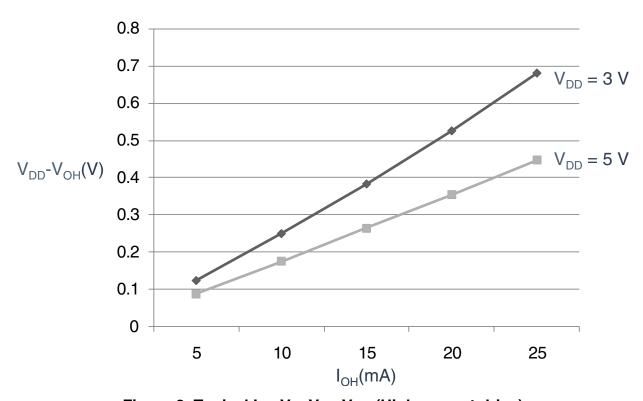


Figure 2. Typical I_{OH} Vs. V_{DD} - V_{OH} (High current drive)

Nonswitching electrical specifications

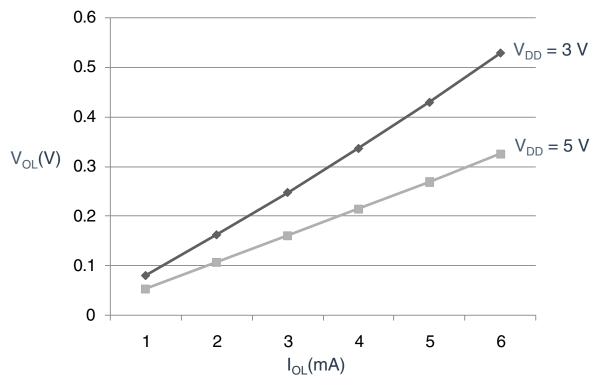


Figure 3. Typical I_{OL} Vs. V_{OL}

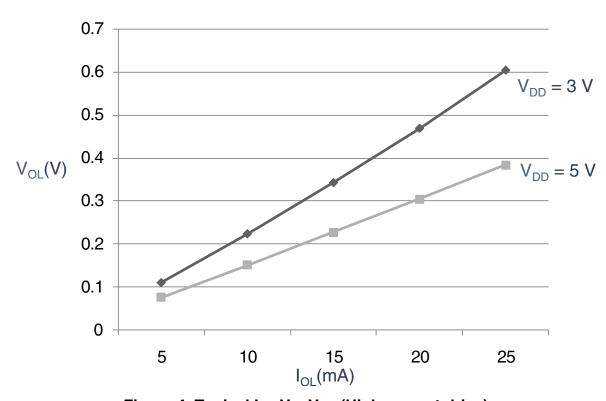


Figure 4. Typical I_{OL} Vs. V_{OL} (High current drive)

5.1.2 Supply current characteristics

This section includes information about power supply current in various operating modes.

Table 4. Supply current characteristics

Num	С	Parameter	Symbol	Bus Freq	V _{DD} (V)	Typical ¹	Max	Unit	Temp
1	С	Run supply current FEI	RI _{DD}	20 MHz	5	5.43	_	mA	-40 to 105 °C
	С	mode, all modules on; run from flash		10 MHz		3.46	_		
		nom nasn		1 MHz		1.71	_		
	С			20 MHz	3	5.35	_		
	С			10 MHz		3.45	_		
				1 MHz		1.69	_		
2	С	Run supply current FEI	RI _{DD}	20 MHz	5	4.51	_	mA	-40 to 105 °C
	С	mode, all modules off and gated; run from flash		10 MHz		3.01	_		
		gated, full from flash		1 MHz		1.68	_		
	С			20 MHz	3	4.47	_		
	С			10 MHz		2.99	_		
				1 MHz		1.65	_		
3	Р	Run supply current FBE	RI _{DD}	20 MHz	5	5.31	7.41	mA	-40 to 105 °C
	С	mode, all modules on; run from RAM		10 MHz		3.17	_		
		HOITHAN		1 MHz		1.25	_		
	С			20 MHz	3	5.29	_		
	С			10 MHz		3.17	_		
				1 MHz		1.24	_		
4	Р	Run supply current FBE	RI _{DD}	20 MHz	5	4.39	6.59	mA	-40 to 105 °C
	С	mode, all modules off and gated; run from RAM		10 MHz		2.71	_		
		gated, full from Fixin		1 MHz		1.21	_		
	С			20 MHz	3	4.39	_		
	С			10 MHz		2.71	_		
				1 MHz		1.20	_		
5	С	Wait mode current FEI	WI _{DD}	20 MHz	5	3.62	_	mA	-40 to 105 °C
	С	mode, all modules on		10 MHz		2.27	_		
				1 MHz		1.11	_		
	С			20 MHz	3	3.61	_		
				10 MHz		2.31	_		
				1 MHz		1.10	_		
6	С	Stop3 mode supply	S3I _{DD}	_	5	5.4	_	μΑ	-40 to 105 °C
	С	current no clocks active (except 1 kHz LPO clock)		_	3	1.40	_		-40 to 105 °C

Table 4. Supply current characteristics (continued)

Num	С	Parameter	Symbol	Bus Freq	V _{DD} (V)	Typical ¹	Max	Unit	Temp
7	C	ADC adder to stop3	_	_	5	96.0	_	μΑ	-40 to 105 °C
	С	ADLPC = 1	_	_	3	88.3	_		
		ADLSMP = 1							
		ADCO = 1							
		MODE = 10B							
		ADICLK = 11B							
8	С	LVD adder to stop3 ²	_	_	5	129	_	μΑ	-40 to 105 °C
	С				3	126	_		

- 1. Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.
- 2. LVD is periodically woken up from stop3 by 5% duty cycle. The period is equal to or less than 2 ms.

5.1.3 EMC performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

5.2 Switching specifications

5.2.1 Control timing

Table 5. Control timing

Num	С	Rating	Symbol	Min	Typical ¹	Max	Unit
1	Р	Bus frequency (t _{cyc} = 1/f _{Bus})	f _{Bus}	DC	_	20	MHz
2	Р	Internal low power oscillator frequency	f _{LPO}	0.67	1.0	1.25	KHz
3	D	External reset pulse width ²	t _{extrst}	1.5 ×	_	_	ns
				t _{Self_reset}			
4	D	Reset low drive	t _{rstdrv}	$34 \times t_{cyc}$	_	_	ns
5	D	BKGD/MS setup time after issuing background debug force reset to enter user or BDM modes	t _{MSSU}	500	_	_	ns
6	D	BKGD/MS hold time after issuing background debug force reset to enter user or BDM modes ³	t _{MSH}	100	_	_	ns

Table 5. Control timing (continued	Table 5.	Control	timing	(continued
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Num	С	Rating	J	Symbol	Min	Typical ¹	Max	Unit
7	path ²			t _{ILIH}	100	_	_	ns
			Synchronous path ⁴	t _{IHIL}	$1.5 \times t_{cyc}$	_	_	ns
8	D	Keyboard interrupt pulse width	Asynchronous path ²	t _{ILIH}	100	_	_	ns
	D		Synchronous path	t _{IHIL}	$1.5 \times t_{cyc}$	_	_	ns
9	С	Port rise and fall time -	_	t _{Rise}	_	10.2	_	ns
	Normal drive strength (HDRVE_PTXx = 0) (load = 50 pF) ⁵			t _{Fall}	_	9.5	_	ns
	С	Port rise and fall time -	_	t _{Rise}	_	5.4	_	ns
	С	Extreme high drive strength (HDRVE_PTXx = 1) (load = 50 pF) ⁵		t _{Fall}	_	4.6	_	ns

- 1. Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.
- 2. This is the shortest pulse that is guaranteed to be recognized as a reset pin request.
- 3. To enter BDM mode following a POR, BKGD/MS must be held low during the powerup and for a hold time of t_{MSH} after V_{DD} rises above V_{LVD} .
- 4. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized.
- 5. Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels. Temperature range -40 °C to 105 °C.

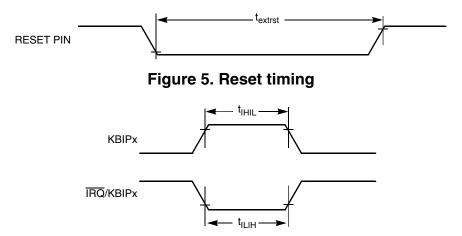


Figure 6. IRQ/KBIPx timing

5.2.2 Debug trace timing specifications

Table 6. Debug trace operating behaviors

Symbol	Description	Min.	Max.	Unit
t _{cyc}	Clock period	Frequency	MHz	
t _{wi}	Low pulse width	2	_	ns
t _{wh}	High pulse width	2	_	ns

Table 6. Debug trace operating behaviors (continued)

Symbol	Description	Min.	Max.	Unit
t _r	Clock and data rise time	_	3	ns
t _f	Clock and data fall time	_	3	ns
t _s	Data setup	3	_	ns
t _h	Data hold	2	_	ns

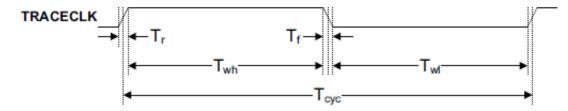


Figure 7. TRACE_CLKOUT specifications

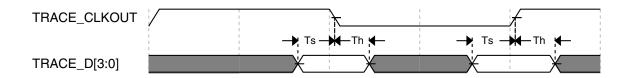


Figure 8. Trace data specifications

5.2.3 FTM module timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 7. FTM input timing

No.	С	Function	Symbol	Min	Max	Unit
1	D	External clock frequency	f _{TCLK}	0	f _{Bus} /4	Hz
2	D	External clock period	t _{TCLK}	4	_	t _{cyc}
3	D	External clock high time	t _{clkh}	1.5	_	t _{cyc}
4	D	External clock low time	t _{clkl}	1.5	_	t _{cyc}
5	D	Input capture pulse width	t _{ICPW}	1.5	_	t _{cyc}

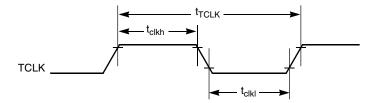


Figure 9. Timer external clock

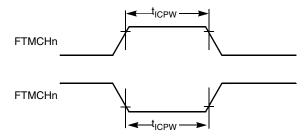


Figure 10. Timer input capture pulse

5.3 Thermal specifications

5.3.1 Thermal characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Rating	Symbol	Value	Unit					
Operating temperature range (packaged)	T _A	T _L to T _H -40 to 105	°C					
Junction temperature range	T _J	-40 to 150	°C					
Thermal resistance single-layer board								
20-pin SOIC	θ_{JA}	83	°C/W					
16-pin TSSOP	θ_{JA}	131	°C/W					
	Thermal resistance	e four-layer board						
20-pin SOIC	θ_{JA}	55	°C/W					
16-pin TSSOP	θ_{JA}	89	°C/W					

Table 8. Thermal characteristics

Peripheral operating requirements and behaviors

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_{J} = T_{A} + (P_{D} \times \theta_{JA})$$

Where:

 T_A = Ambient temperature, °C

 θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W

$$P_D = P_{int} + P_{I/O}$$

 $P_{int} = I_{DD} \times V_{DD}$, Watts - chip internal power

 $P_{I/O}$ = Power dissipation on input and output pins - user determined

For most applications, $P_{I/O} \ll P_{int}$ and can be neglected. An approximate relationship between P_D and T_I (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_I + 273 \, ^{\circ}C)$$

Solving the equations above for K gives:

$$K = P_D \times (T_A + 273 \text{ }^{\circ}\text{C}) + \theta_{IA} \times (P_D)^2$$

where K is a constant pertaining to the particular part. K can be determined by measuring P_D (at equilibrium) for a known T_A . Using this value of K, the values of P_D and T_J can be obtained by solving the above equations iteratively for any value of T_A .

6 Peripheral operating requirements and behaviors

6.1 External oscillator (XOSC) and ICS characteristics

Table 9. XOSC and ICS specifications (temperature range = -40 to 105 °C ambient)

Num	С	C	Characteristic	Symbol	Min	Typical ¹	Max	Unit
1	С	Oscillator	Low range (RANGE = 0)	f _{lo}	32	_	40	kHz
	С	crystal or resonator	High range (RANGE = 1) FEE or FBE mode ²	f _{hi}	4	_	20	MHz
	С		High range (RANGE = 1), high gain (HGO = 1), FBELP mode	f _{hi}	4	_	20	MHz
	С		High range (RANGE = 1), low power (HGO = 0), FBELP mode	f _{hi}	4	_	20	MHz
2	D	Lo	oad capacitors	C1, C2		See Note ³	•	

Table 9. XOSC and ICS specifications (temperature range = -40 to 105 °C ambient) (continued)

Num	С	C	haracteristic	Symbol	Min	Typical ¹	Max	Unit
3	D	Feedback resistor	Low Frequency, Low-Power Mode ⁴	R _F	_	_	_	ΜΩ
			Low Frequency, High-Gain Mode		_	10	_	ΜΩ
			High Frequency, Low- Power Mode		_	1	_	ΜΩ
			High Frequency, High-Gain Mode		_	1	_	ΜΩ
4	D	Series resistor -	Low-Power Mode ⁴	R _S	_	_	_	kΩ
		Low Frequency	High-Gain Mode		_	200	_	kΩ
5	D	Series resistor - High Frequency	Low-Power Mode ⁴	R _S	_	_	_	kΩ
	D	Series resistor -	4 MHz		_	0	_	kΩ
	D	High Frequency,	8 MHz		_	0	_	kΩ
	D	High-Gain Mode	16 MHz		_	0	_	kΩ
6	С	Crystal start-up	Low range, low power	t _{CSTL}	_	1000	_	ms
	= 32.7	time Low range = 32.768 KHz	Low range, high power		_	800	_	ms
		crystal; High	High range, low power	t _{CSTH}	_	3	_	ms
	С	range = 20 MHz crystal ⁵ , ⁶	High range, high power		_	1.5	_	ms
7	Т	Internal re	eference start-up time	t _{IRST}	_	20	50	μs
8	D	Square wave	FEE or FBE mode ²	f _{extal}	0.03125	_	5	MHz
	D	input clock frequency	FBELP mode		0	_	20	MHz
9	Р	Average inter	nal reference frequency - trimmed	f _{int_t}	_	32.768	_	kHz
10	Р	DCO output fi	requency range - trimmed	f _{dco_t}	16	_	20	MHz
11	Р	Total deviation of DCO output	Over full voltage and temperature range	Δf_{dco_t}	_	_	±2.0	%f _{dco}
	С	from trimmed frequency ⁵	Over fixed voltage and temperature range of 0 to 70 °C				±1.0	
12	С	FLL a	cquisition time ⁵ , ⁷	t _{Acquire}	_	_	2	ms
13	С		tter of DCO output clock d over 2 ms interval) ⁸	C_{Jitter}	_	0.02	0.2	%f _{dco}

- 1. Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.
- 2. When ICS is configured for FEE or FBE mode, input clock source must be divisible using RDIV to within the range of 31.25 kHz to 39.0625 kHz.
- 3. See crystal or resonator manufacturer's recommendation.
- Load capacitors (C₁,C₂), feedback resistor (R_F) and series resistor (R_S) are incorporated internally when RANGE = HGO = 0.
- 5. This parameter is characterized and not tested on each device.
- 6. Proper PC board layout procedures must be followed to achieve specifications.

Peripheral operating requirements and behaviors

- 7. This specification applies to any time the FLL reference source or reference divider is changed, trim value changed, DMX32 bit is changed, DRS bit is changed, or changing from FLL disabled (FBELP, FBILP) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
- 8. Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{Bus}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

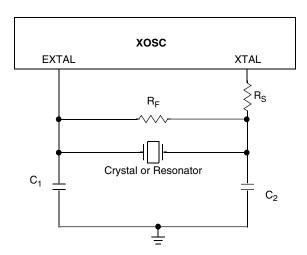


Figure 11. Typical crystal or resonator circuit

6.2 NVM specifications

This section provides details about program/erase times and program/erase endurance for the flash and EEPROM memories.

С	Characteristic	Symbol	Min ¹	Typical ²	Max ³	Unit ⁴
D	Supply voltage for program/erase -40 °C to 105 °C	V _{prog/erase}	2.7	_	5.5	V
D	Supply voltage for read operation	V _{Read}	2.7	_	5.5	V
D	NVM Bus frequency	f _{NVMBUS}	1	_	25	MHz
D	NVM Operating frequency	f _{NVMOP}	0.8	_	1.05	MHz
D	Erase Verify All Blocks	t _{VFYALL}	_	_	17030	t _{cyc}
D	Erase Verify Flash Block	t _{RD1BLK}	_	_	16977	t _{cyc}
D	Erase Verify EEPROM Block	t _{RD1BLK}	_	_	843	t _{cyc}
D	Erase Verify Flash Section	t _{RD1SEC}	_	_	517	t _{cyc}
D	Erase Verify EEPROM Section	t _{DRD1SEC}	0.10	0.10	0.11	ms
D	Read Once	t _{RDONCE}	_	_	455	t _{cyc}
D	Program Flash (2 word)	t _{PGM2}	0.12	0.12	0.14	ms
D	Program Flash (4 word)	t _{PGM4}	0.20	0.21	0.24	ms
D	Program Once	t _{PGMONCE}	0.20	0.21	0.24	ms
D	Program EEPROM (1 Byte)	t _{DPGM1}	0.02	0.02	0.02	ms

Table 10. Flash characteristics

Table 10. Flash characteristics (continued)

С	Characteristic	Symbol	Min ¹	Typical ²	Max ³	Unit ⁴
D	Program EEPROM (2 Byte)	t _{DPGM2}	0.17	0.18	0.20	ms
D	Erase All Blocks	t _{ERSALL}	96.01	100.78	125.80	ms
D	Erase Flash Block	t _{ERSBLK}	95.98	100.75	125.76	ms
D	Erase Flash Sector	t _{ERSPG}	19.10	20.05	25.05	ms
D	Erase EEPROM Sector	t _{DERSPG}	4.81	5.05	6.30	ms
D	Unsecure Flash	t _{UNSECU}	96.01	100.78	125.80	ms
D	Verify Backdoor Access Key	t _{VFYKEY}	_	_	469	t _{cyc}
D	Set User Margin Level	t _{MLOADU}	_	_	442	t _{cyc}
С	FLASH Program/erase endurance T_L to T_H = -40 °C to 105 °C	n _{FLPE}	10 k	100 k	_	Cycles
С	EEPROM Program/erase endurance TL to TH = -40 °C to 105 °C	n _{FLPE}	50 k	500 k	_	Cycles
С	Data retention at an average junction temperature of T _{Javg} = 85°C after up to 10,000 program/erase cycles	t _{D_ret}	15	100	_	years

- 1. Minimun times are based on maximum $f_{\mbox{\scriptsize NVMOP}}$ and maximum $f_{\mbox{\scriptsize NVMBUS}}$
- 2. Typical times are based on typical f_{NVMOP} and maximum f_{NVMBUS}
- 3. Maximum times are based on minimum $f_{\mbox{\scriptsize NVMOP}}$ and maximum $f_{\mbox{\scriptsize NVMBUS}}$
- 4. $t_{cyc} = 1 / f_{NVMBUS}$

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see the Memory section.

6.3 Analog

6.3.1 ADC characteristics

Table 11. 5 V 12-bit ADC operating conditions

Characteri stic	Conditions	Symb	Min	Typ ¹	Max	Unit	Comment
Supply	Absolute	V_{DDA}	2.7	_	5.5	V	_
voltage	Delta to V _{DD} (V _{DD} -V _{DDAD})	ΔV_{DDA}	-100	0	+100	mV	
Ground voltage	Delta to V _{SS} (V _{SS} -V _{SSA}) ²	ΔV _{SSA}	-100	0	+100	mV	
Input voltage		V _{ADIN}	V _{REFL}	_	V _{REFH}	V	
Input capacitance		C _{ADIN}	_	4.5	5.5	pF	

Table 11. 5 V 12-bit ADC operating conditions (continued)

Characteri stic	Conditions	Symb	Min	Typ ¹	Max	Unit	Comment
Input resistance		R _{ADIN}	_	3	5	kΩ	_
Analog source	12-bit mode • f _{ADCK} > 4 MHz	R _{AS}	_	_	2 5	kΩ	External to MCU
resistance	• f _{ADCK} < 4 MHz 10-bit mode	_	<u> </u>	_	5		
	• f _{ADCK} > 4 MHz		_	_	5		
	• f _{ADCK} < 4 MHz		_	_	10		
	8-bit mode		_	_	10		
	(all valid f _{ADCK})						
ADC	High speed (ADLPC=0)	f _{ADCK}	0.4	_	8.0	MHz	_
conversion clock frequency	Low power (ADLPC=1)		0.4	_	4.0		

- 1. Typical values assume $V_{DDA} = 5.0 \text{ V}$, Temp = 25°C, $f_{ADCK} = 1.0 \text{ MHz}$ unless otherwise stated. Typical values are for reference only and are not tested in production.
- 2. DC potential difference.

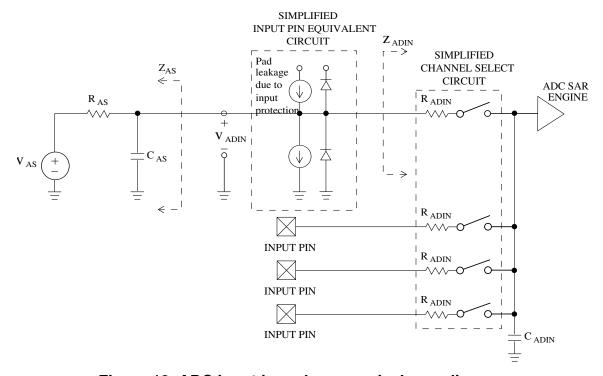


Figure 12. ADC input impedance equivalency diagram

Table 12. 12-bit ADC Characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Characteristic	Conditions	С	Symb	Min	Typ ¹	Max	Unit
Supply current		Т	I _{DDA}	_	133	_	μΑ
ADLPC = 1							
ADLSMP = 1							
ADCO = 1							
Supply current		Т	I _{DDA}	_	218	_	μΑ
ADLPC = 1							
ADLSMP = 0							
ADCO = 1							
Supply current		Т	I _{DDA}	_	327	_	μΑ
ADLPC = 0							
ADLSMP = 1							
ADCO = 1							
Supply current		Т	I _{DDAD}	_	582	990	μΑ
ADLPC = 0							
ADLSMP = 0							
ADCO = 1							
Supply current	Stop, reset, module off	Т	I _{DDA}	_	0.011	1	μА
ADC asynchronous clock source	High speed (ADLPC = 0)	Р	f _{ADACK}	2	3.3	5	MHz
	Low power (ADLPC = 1)			1.25	2	3.3	
Conversion time (including sample	Short sample (ADLSMP = 0)	Т	t _{ADC}	_	20	_	ADCK cycles
time)	Long sample (ADLSMP = 1)			_	40	_	
Sample time	Short sample (ADLSMP = 0)	Т	t _{ADS}	_	3.5	_	ADCK cycles
	Long sample (ADLSMP = 1)			_	23.5	_	
Total unadjusted	12-bit mode	Т	E _{TUE}	_	±5.0	_	LSB ³
Error ²	10-bit mode	Р		_	±1.5	±2.0	
	8-bit mode	Р		_	±0.7	±1.0	
Differential Non-	12-bit mode	Т	DNL	_	±1.0	_	LSB ³
Liniarity	10-bit mode ⁴	Р		_	±0.25	±0.5	
	8-bit mode ⁴	Р		_	±0.15	±0.25	
Integral Non-Linearity	12-bit mode	Т	INL	_	±1.0	_	LSB ³
	10-bit mode	Т		_	±0.3	±0.5	
	8-bit mode	Т		_	±0.15	±0.25	

Table 12. 12-bit ADC Characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Characteristic	Conditions	С	Symb	Min	Typ ¹	Max	Unit
Zero-scale error ⁵	12-bit mode	С	E _{ZS}	_	±2.0	_	LSB ³
	10-bit mode	Р		_	±0.25	±1.0	
	8-bit mode	Р		_	±0.65	±1.0	
Full-scale error ⁶	12-bit mode	Т	E _{FS}	_	±2.5	_	LSB ³
	10-bit mode	Т		_	±0.5	±1.0	
	8-bit mode	Т		_	±0.5	±1.0	
Quantization error	≤12 bit modes	D	EQ	_	_	±0.5	LSB ³
Input leakage error ⁷	all modes	D	E _{IL}		I _{In} * R _{AS}		mV
Temp sensor slope	-40°C– 25°C	D	m	_	3.266	_	mV/°C
	25°C- 125°C			_	3.638	_	
Temp sensor voltage	25°C	D	V _{TEMP25}	_	1.396	_	V

- 1. Typical values assume V_{DDA} = 5.0 V, Temp = 25°C, f_{ADCK}=1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
- 2. Includes quantization.
- 3. $1 LSB = (V_{REFH} V_{REFL})/2^{N}$
- 4. Monotonicity and no-missing-codes guaranteed in 10-bit and 8-bit modes
- 5. $V_{ADIN} = V_{SSA}$
- 6. $V_{ADIN} = V_{DDA}$
- 7. I_{ln} = leakage current (refer to DC characteristics)

6.3.2 Analog comparator (ACMP) electricals

Table 13. Comparator electrical specifications

С	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage	V_{DDA}	2.7	_	5.5	V
Т	Supply current (Operation mode)	I _{DDA}	_	10	20	μΑ
D	Analog input voltage	V _{AIN}	V _{SS} - 0.3	_	V_{DDA}	V
Р	Analog input offset voltage	V _{AIO}	_	_	40	mV
С	Analog comparator hysteresis (HYST=0)	V _H	_	15	20	mV
С	Analog comparator hysteresis (HYST=1)	V _H	_	20	30	mV
Т	Supply current (Off mode)	I _{DDAOFF}	_	60	_	nA
С	Propagation Delay	t _D	_	0.4	1	μs

Dimensions

Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to www.freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
16-pin TSSOP	98ASH70247A
20-pin SOIC	98ASB42343B

Pinout

Signal multiplexing and pin assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

Table 14. Pin availability by package pin-count Din Number Lowest Priority --- Highest

Pin N	umber	Lowest Priority <> Highest				
20-SOIC	16-TSSOP	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
1	1	PTA5	IRQ	FTM1CH0	_	RESET
2	2	PTA4	_	ACMPO	BKGD	MS
3	3	_	_	_	_	V _{DD}
4	4	_	_	_	_	V _{SS}
5	5	PTB7	_	_	_	EXTAL
6	6	PTB6	_	_	_	XTAL
7	7	PTB5 ¹	_	FTM1CH1	_	_
8	8	PTB4 ¹	_	FTM1CH0	_	_
9	_	PTC3	_	_	_	_
10	_	PTC2	_	_	_	_
11	_	PTC1	_	_	_	_
12	_	PTC0	_	_	_	_

Table 14.	Pin availability	by package	pin-count	(continued)
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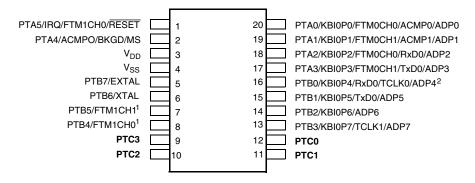
Pin N	lumber	Lowest Priority <> Highest						
20-SOIC	16-TSSOP	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4		
13	9	PTB3	KBI0P7	_	TCLK1	ADP7		
14	10	PTB2	KBI0P6	_	_	ADP6		
15	11	PTB1	KBI0P5	TxD0	_	ADP5		
16	12	PTB0 ²	KBI0P4	RxD0	TCLK0	ADP4		
17	13	PTA3	KBI0P3	FTM0CH1	TxD0	ADP3		
18	14	PTA2	KBI0P2	FTM0CH0	RxD0	ADP2		
19	15	PTA1	KBI0P1	FTM0CH1	ACMP1	ADP1		
20	16	PTA0	KBI0P0	FTM0CH0	ACMP0	ADP0		

- 1. This is a high current drive pin when operated as output.
- 2. This is a true open-drain pin when operated as output.

Note

When an alternative function is first enabled, it is possible to get a spurious edge to the module. User software must clear any associated flags before interrupts are enabled. The table above illustrates the priority if multiple modules are enabled. The highest priority module will have control over the pin. Selecting a higher priority pin function with a lower priority function already enabled can cause spurious edges to the lower priority module. Disable all modules that share a pin before enabling another module.

8.2 Device pin assignment



Pins in **bold** are not available on less pin-count packages.

- 1. High source/sink current pins
- 2. True open drain pins

Figure 13. MC9S08PA4 20-pin SOIC package

PTA5/IRQ/FTM1CH0/RESET PTA4/ACMPO/BKGD/MS VDD VSS PTB7/EXTAL PTB6/XTAL PTB5/FTM1CH1 ¹	2 3 4 5	6 PTA0/KBI0P0/FTM0CH0/ACMP0/ADP0 5 PTA1/KBI0P1/FTM0CH1/ACMP1/ADP1 4 PTA2/KBI0P2/FTM0CH0/RxD0/ADP2 3 PTA3/KBI0P3/FTM0CH1/TxD0/ADP3 2 PTB0/KBI0P4/RxD0/TCLK0/ADP4 ² 1 PTB1/KBI0P5/TxD0/ADP5
PTB5/FTM1CH1 ¹ PTB4/FTM1CH0 ¹	1 ~	

Pins in **bold** are not available on less pin-count packages.

1. High source/sink current pins

2. True open drain pins

Figure 14. MC9S08PA4 16-pin TSSOP package

Revision history 9

The following table provides a revision history for this document.

Table 15. Revision history

Rev. No.	Date	Substantial Changes
1	12/2012	Initial public release

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Document Number: MC9S08PA4

Rev. 2, 12/20/2012

